

1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage, T _j = -40 °C to +175 °C			170	V
I _{F(RMS)}	Forward rms current			60	A
I _{F(AV)}	Average forward current	T _c = 150 °C, δ = 0.5	Per diode	20	A
		T _c = 145 °C, δ = 0.5	Per device	40	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal		250	A
P _{ARM}	Repetitive peak avalanche power	t _p = 10 μs, T _j = 125 °C		1015	W
T _{stg}	Storage temperature range			-65 to +175	°C
T _j	Operating junction temperature range ⁽¹⁾			-40 to +175	°C

1. $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Max. value	Unit
R _{th(j-c)}	Junction to case	Per diode	1.20	°C/W
		Total	0.85	
R _{th(c)}	Coupling		0.50	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}	-		30	μA
		T _j = 125 °C		-	7	30	mA
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 20 A	-		0.92	V
		T _j = 125 °C		-	0.69	0.75	
		T _j = 25 °C	I _F = 40 A	-		1.00	
		T _j = 125 °C		-	0.79	0.86	

1. Pulse test: t_p = 5 ms, δ < 2%

2. Pulse test: t_p = 380 μs, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 0.64 \times I_{F(AV)} + 0.0055 \times I_{F(RMS)}^2$$

1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (per diode)

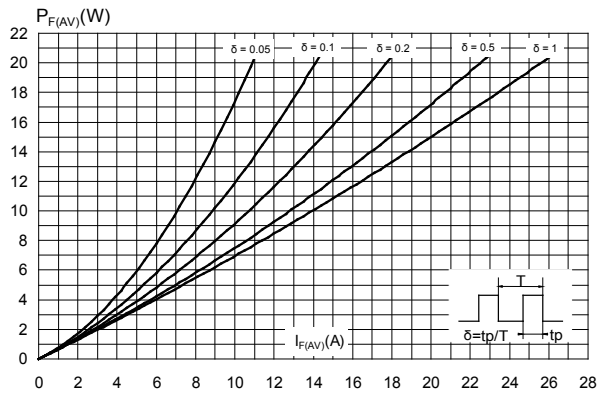


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

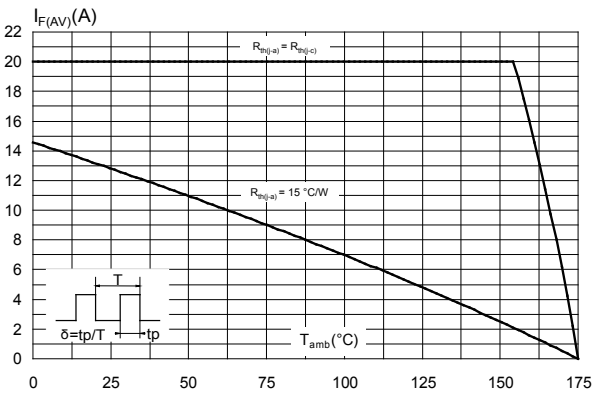


Figure 3. Normalized avalanche power derating versus junction temperature ($T_j = 125^\circ\text{C}$)

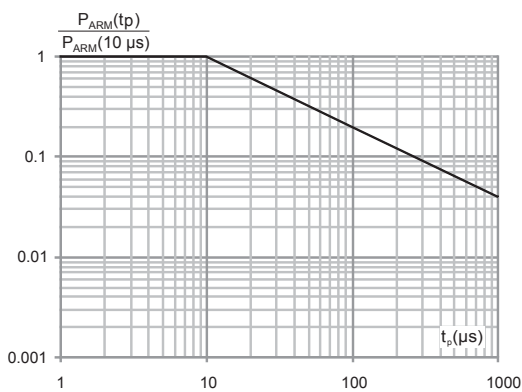


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

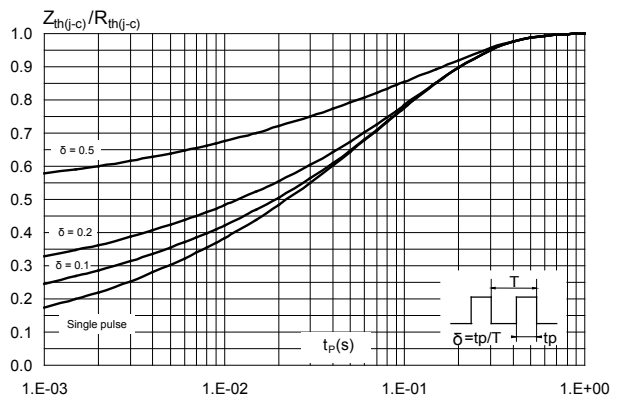


Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

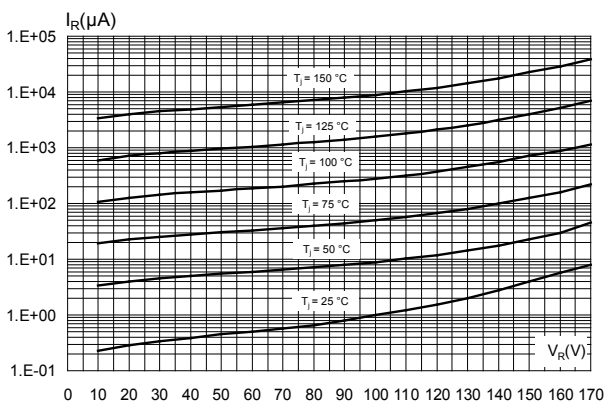


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

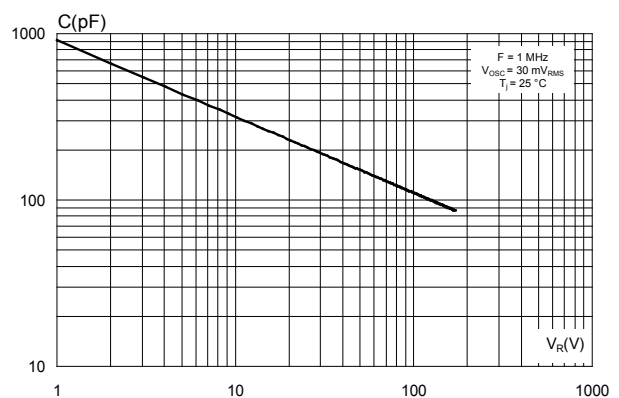


Figure 7. Forward voltage drop versus forward current (per diode, low level)

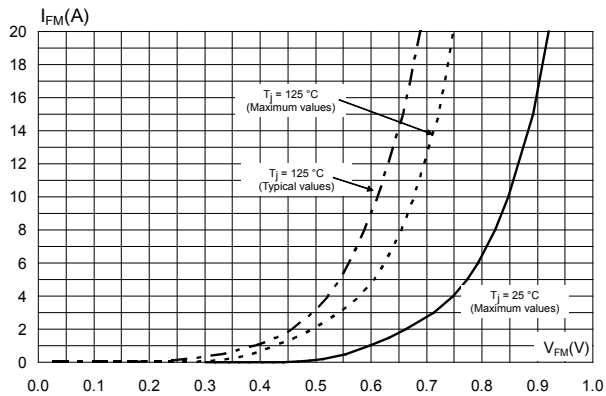


Figure 8. Forward voltage drop versus forward current (per diode, high level)

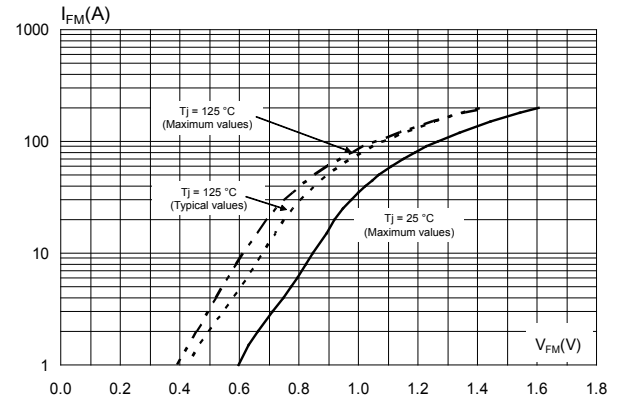
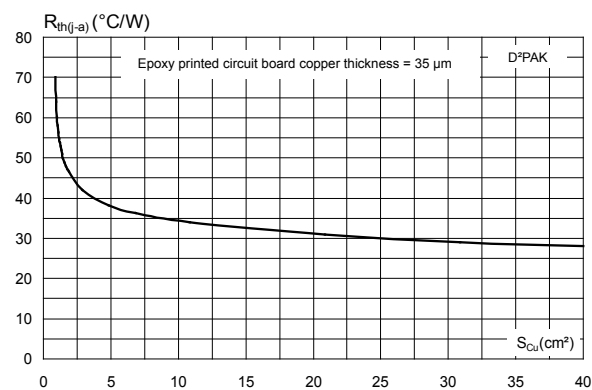


Figure 9. Thermal resistance junction to ambient versus copper surface under tab



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 D²PAK package information

- Epoxy meets UL94, V0.
- Cooling method: by conduction (C)

Figure 10. D²PAK package outline

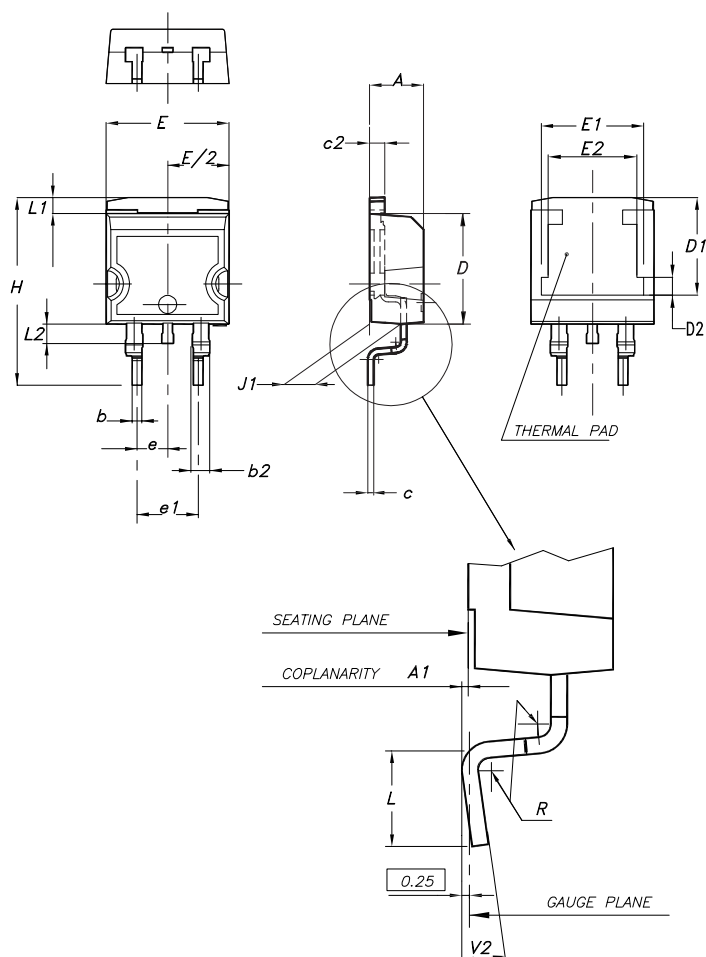
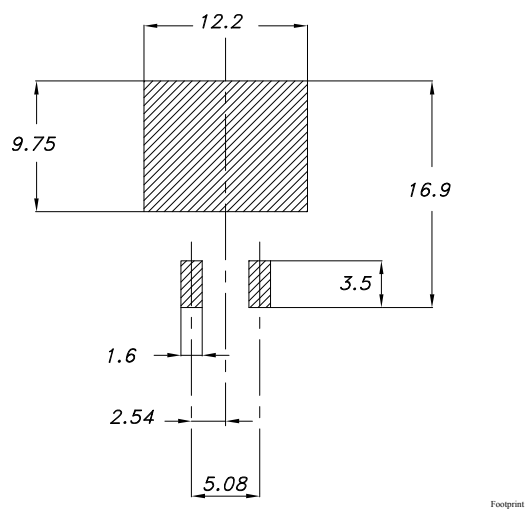


Table 4. D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10		10.40	0.394		0.409
E1	8.50	8.70	8.90	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.4			0.015	
V2	0°		8°	0°		8°

Figure 11. D²PAK recommended footprint (dimensions are in mm)


3 Ordering information

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS40170CGY-TR	STPS40170CGY	D ² PAK	1.48 g	1000	Tape and reel

Revision history

Table 6. Document revision history

Date	Version	Changes
03-Nov-2011	1	Initial release.
09-Apr-2018	2	Removed figure 4 and figure 5. Updated Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified, per diode) and Figure 3. Normalized avalanche power derating versus junction temperature ($T_j = 125\text{ °C}$). Updated Section • Description. Minor text changes to improve readability.

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